PATENT
83388.0002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:
Shin TAMATA, et al
Serial No: 10/090,413
Filed: February 28, 2002
For: PROCESS FOR TREATING PERFLUORIDES

Art Unit: 2812
Examiner: Not Assigned

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to:
Commissioner for Patents
Washington D.C. 20231, on
February 10, 2003
Date of Deposit
Anthony J. Orler, Reg. No. 41,232
Name
02/10/03
Signature Date

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Prior to the first Office Action in the present application, please enter and consider the following amendments and remarks:

IN THE SPECIFICATION:

Please replace the paragraph on pages 1 and 2, starting at line 17 with the following text:

In the semiconductor (semiconductor chip and liquid crystal panel) manufacturing plants, perfluorocompounds are used as etching gas or cleaning gas in the semiconductor manufacturing steps. Perfluorocompounds (hereinafter referred to as PFC) are a general term for the chlorine-free compounds of carbon and fluorine, carbon, hydrogen and fluorine, sulfur and fluorine, and nitrogen and fluorine, such as CF_4, CHF_3, C_2F_6, CH_2F_2, C_3F_8, C_5F_8, SF_6 and NF_3. PFC have a long life time in the atmosphere (10,000 years for C_2F_6 and 3,200 years for SF_6), and they are an earth warming gas with a large warming factor, so that their release into the atmosphere is regulated. Researchers are pursuing studies on the method of decomposing